

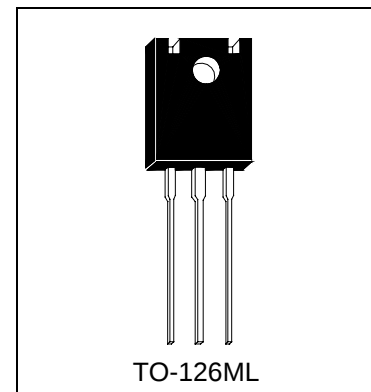


HSB649A

SILICON PNP EPITAXIAL PLANAR TRANSISTOR

Description

Low frequency power amplifier complementary pair with HSD669A.



Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
Storage Temperature -55 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation 1 W
Total Power Dissipation (Tc=25°C) 20 W
- Maximum Voltages and Currents
BVCBO Collector to Base Voltage -180 V
BVCEO Collector to Emitter Voltage -160 V
BVEBO Emitter to Base Voltage -5 V
IC Collector Current (DC) -1.5 A
IC Collector Current (Pulse) -3 A

Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-180	-	-	V	IC=-1mA, IE=0
BVCEO	-160	-	-	V	IC=-10mA, IB=0
BVEBO	-5	-	-	V	IE=-1mA, IC=0
ICBO	-	-	-10	uA	VCB=-160V, IE=0
*VCE(sat)	-	-	-1	V	IC=-500mA, IB=-50mA
*VBE(on)	-	-	-1.5	V	IC=-150mA, VCE=-5V
*hFE1	60	-	200		IC=-150mA, VCE=-5V
*hFE2	30	-	-		IC=-500mA, VCE=-5V
fT	-	140	-	MHz	IC=-150mA, VCE=-5V
Cob	-	27	-	pF	VCB=-10V, f=1MHz, IE=0

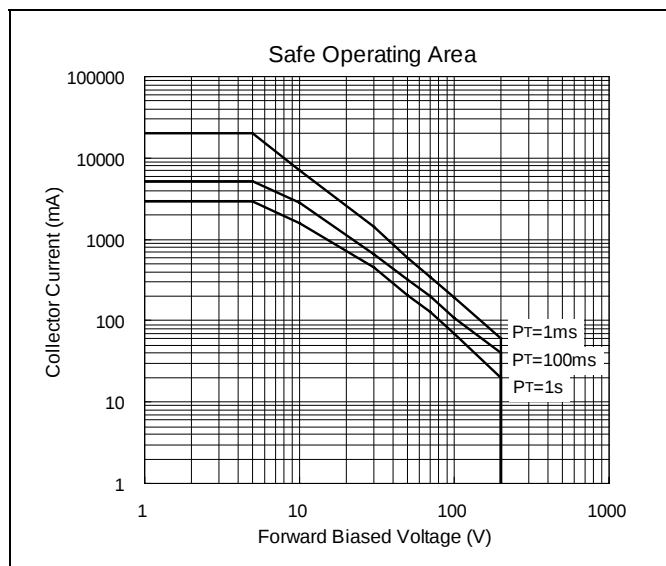
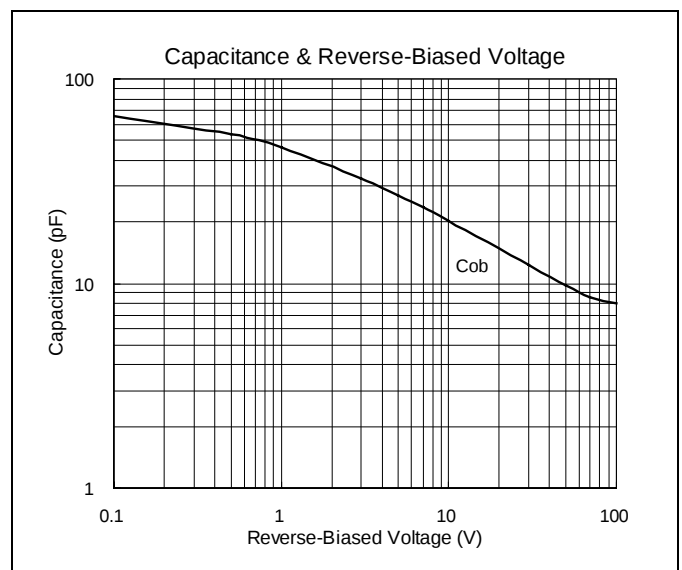
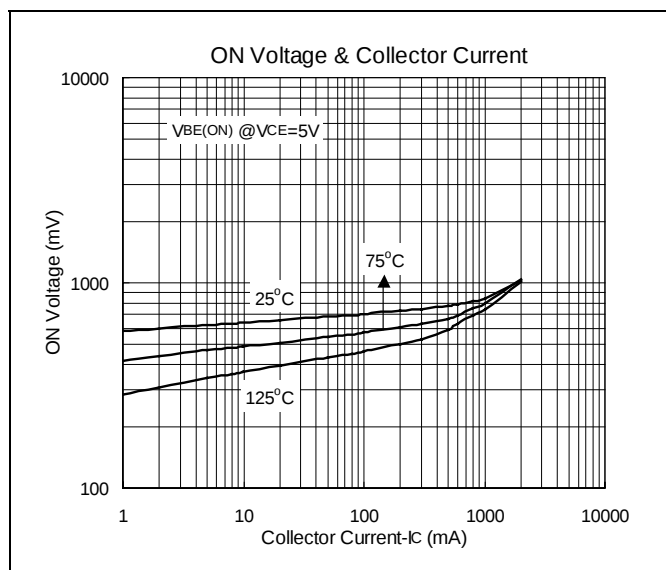
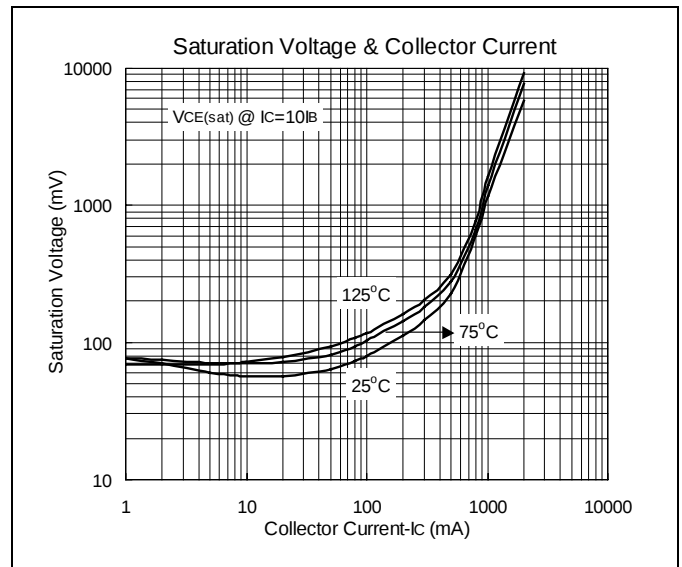
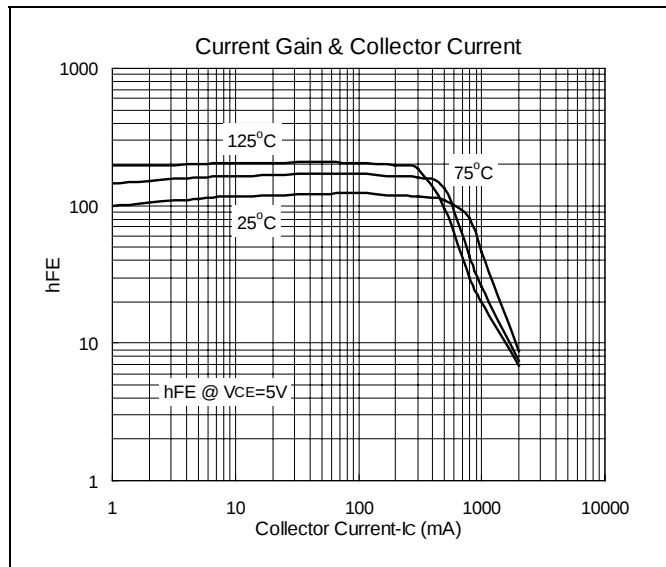
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

Classification Of hFE1

Rank	B	C
Range	60-120	100-200

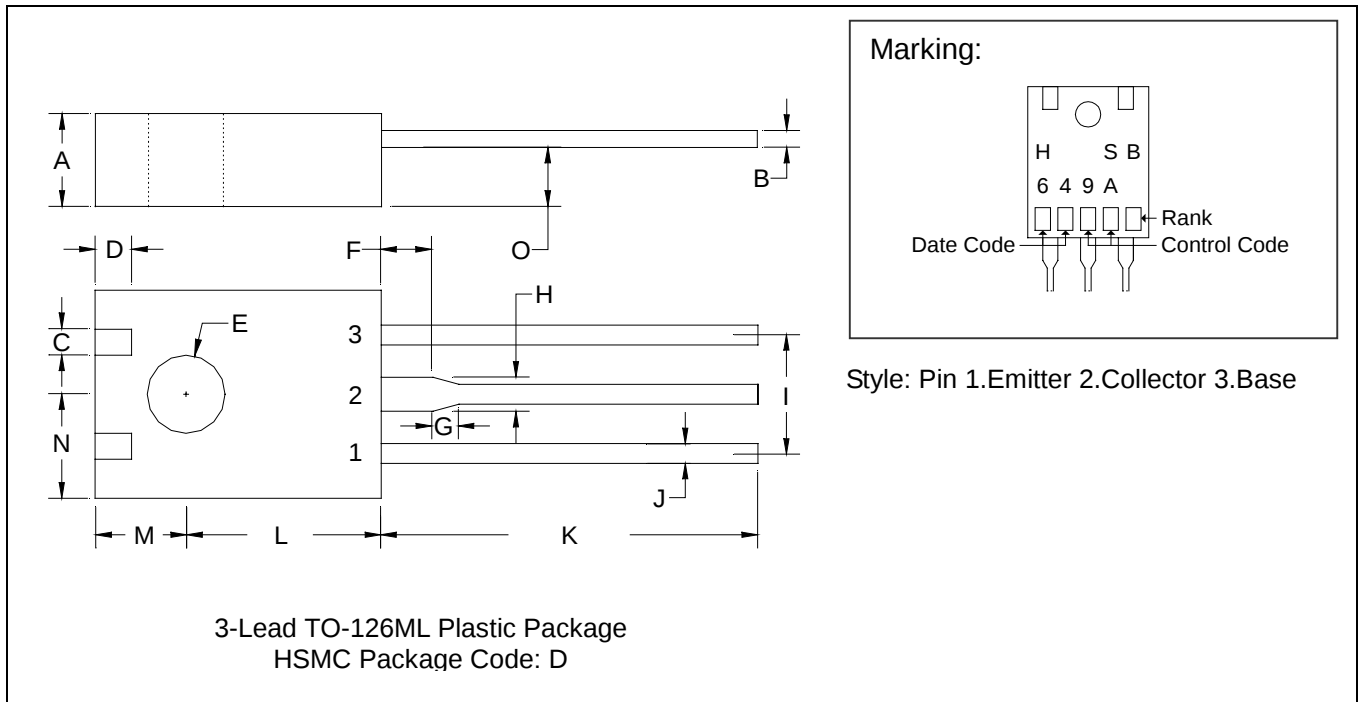


Characteristics Curve





TO-126ML Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1356	0.1457	3.44	3.70	I	-	*0.1795	-	*4.56
B	0.0170	0.0272	0.43	0.69	J	0.0268	0.0331	0.68	0.84
C	0.0344	0.0444	0.87	1.12	K	0.5512	0.5906	14.00	15.00
D	0.0501	0.0601	1.27	1.52	L	0.2903	0.3003	7.37	7.62
E	0.1131	0.1231	2.87	3.12	M	0.1378	0.1478	3.50	3.75
F	0.0737	0.0837	1.87	2.12	N	0.1525	0.1625	3.87	4.12
G	0.0294	0.0494	0.74	1.25	O	0.0740	0.0842	1.88	2.14
H	0.0462	0.0562	1.17	1.42					

Notes: 1.Dimension and tolerance based on our Spec. dated Mar. 6,1995.
2.Controlling dimension: millimeters.
3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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